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- “Structural and chemical disorder in semiconductors under pressure: Evidence in II–VI’s, role of photoactive defects, material predictions”, B. A. Weinstein, G. P. Lindberg, N. Gross, Japan Journal of Applied Physics **56**, 05FA05(1-14) (2017). <http://doi.org/10.7567/Jjap.56.05Fa05>
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